

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

FUJI:1

Application Number

NEW APPLICATION

Applicant(s)

Applicant(s):

Filing Date

January 9, 2001

Group Art Unit

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

"Lowered on-state resistance of lateral power MOSFET with high withstand voltage for Intelligent Power Device"; Uno et al.: The Institute of Electrical Engineers of Japan, EDD-93-21, SPC-93-43; pgs. 21-29; October 7, 1993

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DATE CONSIDERED

9/20/02

EXAMINER

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.